



A Product Line of Diodes Incorporated



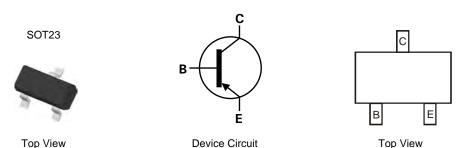
## 30V PNP SILICON PLANAR MEDIUM POWER HIGH PERFORMANCE TRANSISTOR

### **Features and Benefits**

- BV<sub>CEO</sub> > -30V
- I<sub>C</sub> = -1A Continuous Collector Current
- Low saturation voltage V<sub>CE(sat)</sub> < -350mV @ -1A</li>
- R<sub>SAT</sub> = 250mΩ for a low equivalent on-resistance
- Complementary NPN type: FMMT489
- Low equivalent on-resistance; R<sub>CE(sat)</sub> = 250mW @ 1A
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound (Note 2). UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Copper Plated Alloy
  42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)



Top View Pin-Out

## Ordering Information (Note 3)

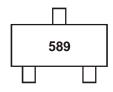
t				
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT589TA	589	7	8	3,000

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com

3. For Packaging Details, go to our website at http://www.diodes.com.

## **Marking Information**



589 = Product Type Marking Code





# Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Collector-Base Voltage		V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage		VCEO	-30	V
Emitter-Base Voltage		V <sub>EBO</sub>	-5	V
Continuous Collector Current	(Note 4)	Ic	-1	A
Peak Pulse Current		ICM	-2	А
Base Current		IB	-200	mA

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 4)	D-	500	mW
Linear Derating Factor	(NOLE 4)	PD	4	mW/°C
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{ ext{ heta}JA}$	250	°C/W
Thermal Resistance, Junction to Lead (Note 5)		R <sub>θJL</sub>	197	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50		_	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 6)	BV <sub>CEO</sub>	-30	_	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5	_	_	V	I <sub>E</sub> = -100μA
Collector Cutoff Current	I <sub>CBO</sub>	—	_	-100	nA	V <sub>CB</sub> = -30V
Collector-Emitter Cutoff Current	I <sub>CES</sub>	—	_	-100	nA	$V_{CES} = -30V$
Emitter Cutoff Current	I <sub>EBO</sub>		_	-100	nA	$V_{EB} = -4V$
ON CHARACTERISTICS (Note 6)						
DC Current Gain	h <sub>FE</sub>	100 100 80 40		 300 	_	$\begin{split} I_{C} &= -1 mA, \ V_{CE} &= -2V \\ I_{C} &= -500 mA, \ V_{CE} &= -2V \\ I_{C} &= -1A, \ V_{CE} &= -2V \\ I_{C} &= -2A, \ V_{CE} &= -2V \end{split}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			-0.25 -0.35 -0.65	v	$I_{C} = -0.5A, I_{B} = -50mA$ $I_{C} = -1A, I_{B} = -100mA$ $I_{C} = -2A, I_{B} = -200mA$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		_	-1.2	V	I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA
Base-Emitter Turn-On Voltage	V <sub>BE(on)</sub>	_	_	-1.1	V	I <sub>C</sub> = -1A, V <sub>CE</sub> = -2V
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>	_	_	15	pF	$V_{CB} = -10V, f = 1MHz$
Current Gain-Bandwidth Product	f <sub>T</sub>	100	_		MHz	$V_{CE} = -5V, I_C = -100mA, f = 100MHz$

4. For a device surface mounted on a 15mm x 15mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured Notes: when operating in a steady-state condition.

5. Thermal resistance from junction to solder-point (at the end of the collector lead).

6. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$ 2%



**Diodes Incorporated** 

td,tr,tf



ts

(ns)

1800

1600

1400

1200

1000

800

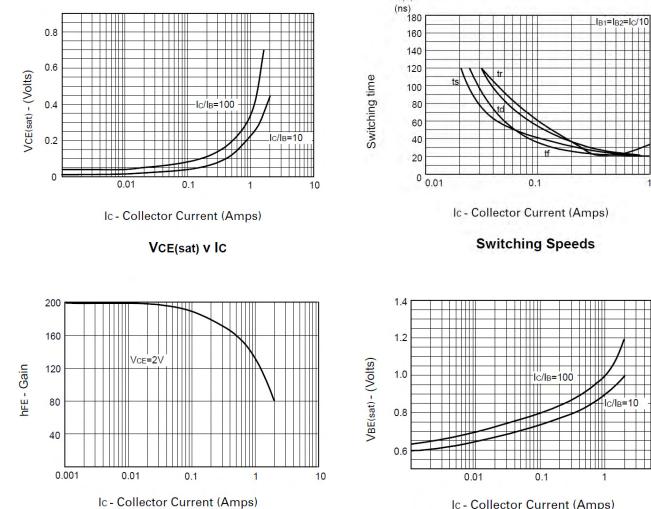
600

400

200

0

1



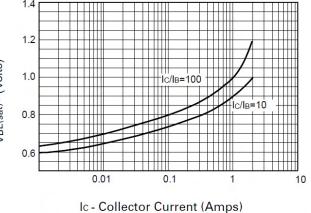
hFE v lC

1.0 Ic/I<sub>B</sub>=10 0.9 VBE - (Volts) 0.8 0.7 -----0.6 0.001 0.01 0.1 1 10

Ic - Collector Current (Amps)

VBE(on) v IC



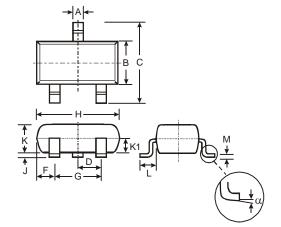


VBE(sat) v IC



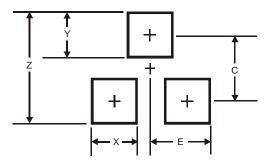


# Package Outline Dimensions



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
К	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
М	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

# Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35





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